

IN THE SPECIFICATION

Please replace the paragraph at page 1, lines 5-9, with the following rewritten paragraph:

WAL This application is a continuation of U.S. application serial no. 09/718,483 filed November 24, 2000, and is ^{Pat. 6,773,687} based upon and claims the benefit of priority from the prior Japanese Patent Application No. 11-333433, filed November 24, 1999, the entire contents of each of which are incorporated herein by reference.

Please replace the paragraph at page 1, lines 12-17, with the following rewritten paragraph:

The present invention relates to an exhaust apparatus for a process gas, which is used in combination with a process apparatus for forming [[a or]] a layer on an object to be processed using the process gas, and relates to a method of removing an impurity gas (unprocessed gas, non-reacted process gas) formed by a process gas.

Please replace the paragraph at page 16, lines 10-21, with the following rewritten paragraph:

To the deposition of the Ti film generally consumes approximately 10% of the TiCl_4 gas, and the remaining gas (about [[96%]] 90%) as a non-reaction gas and reaction by-products of TiCl_2 , TiCl_3 and HCl are fed into the exhaust pipe 30 from the exhaust ports 28 together with the exhaust gas by the vacuum pump 33. The exhaust gas further flows down in the order of the trap mechanism 32, the vacuum pump 33 and the eliminator 34. In this case, the non-reacting TiCl_4 gas, and the reaction by-products, have a relatively high vapor pressure, which are not generally possible to be sufficiently removed by the trap mechanism 32.